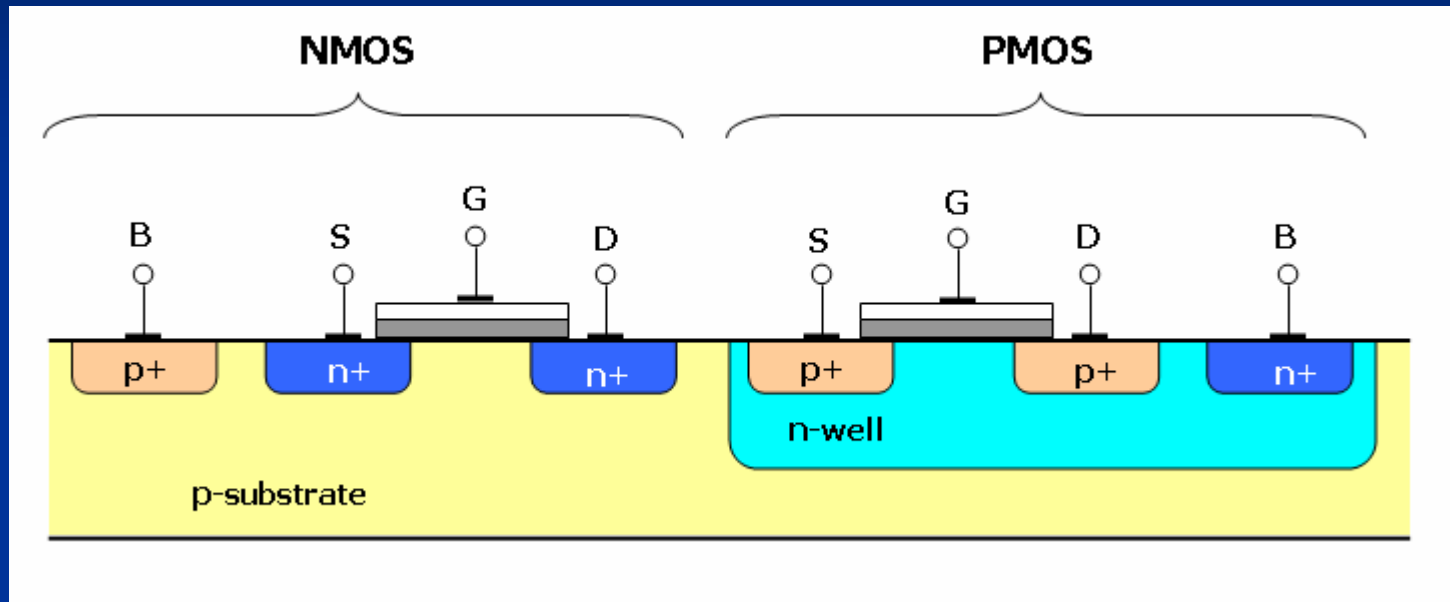


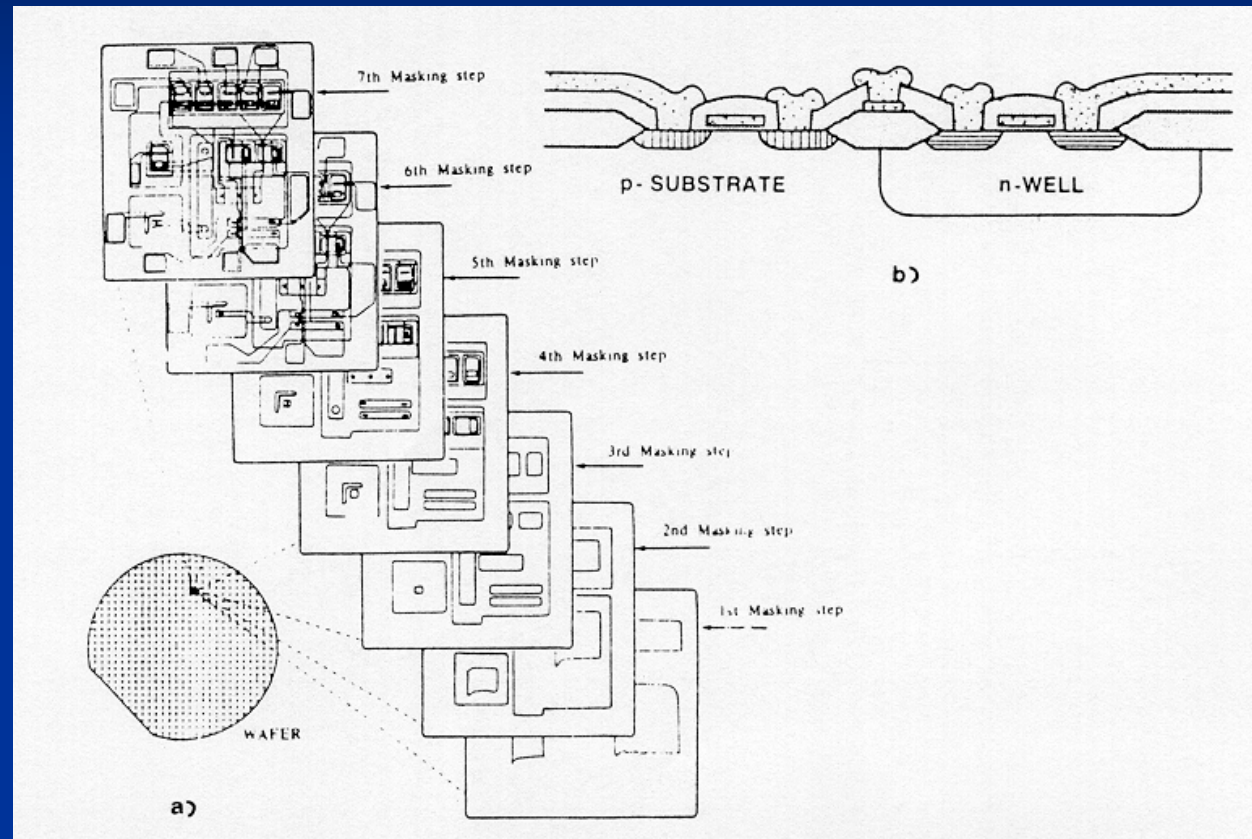
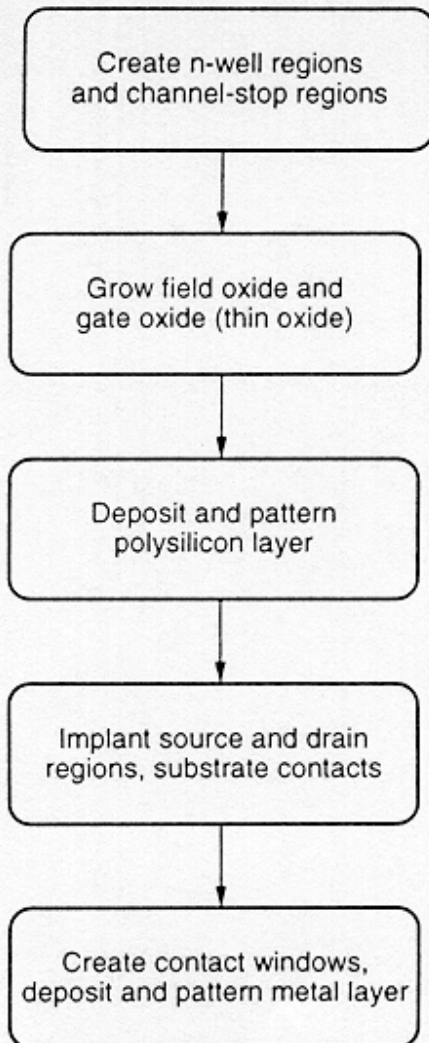
# VLSI Design

Fabrication Process

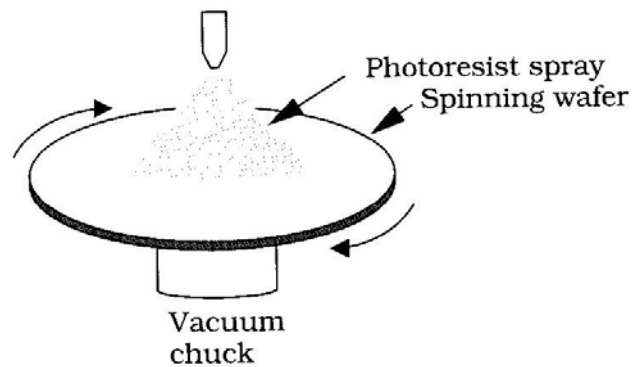
# CMOS Transistors



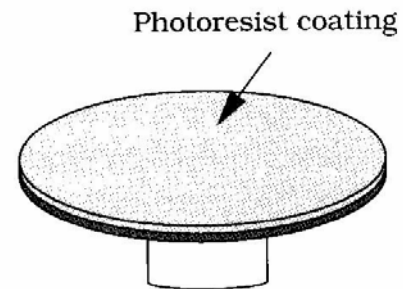
# Overview



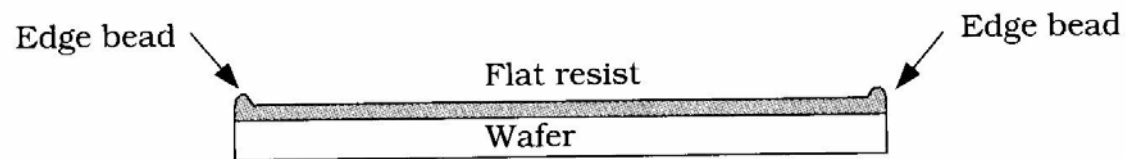
# Coating



(a) Resist application

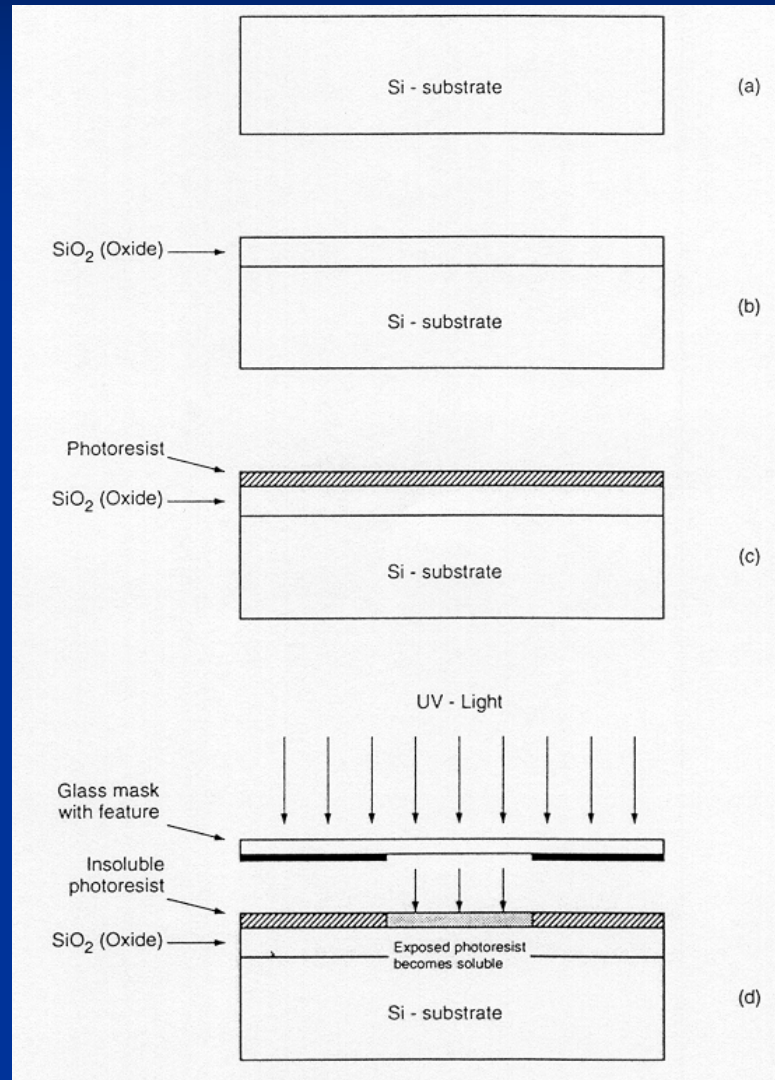


(b) Coated wafer

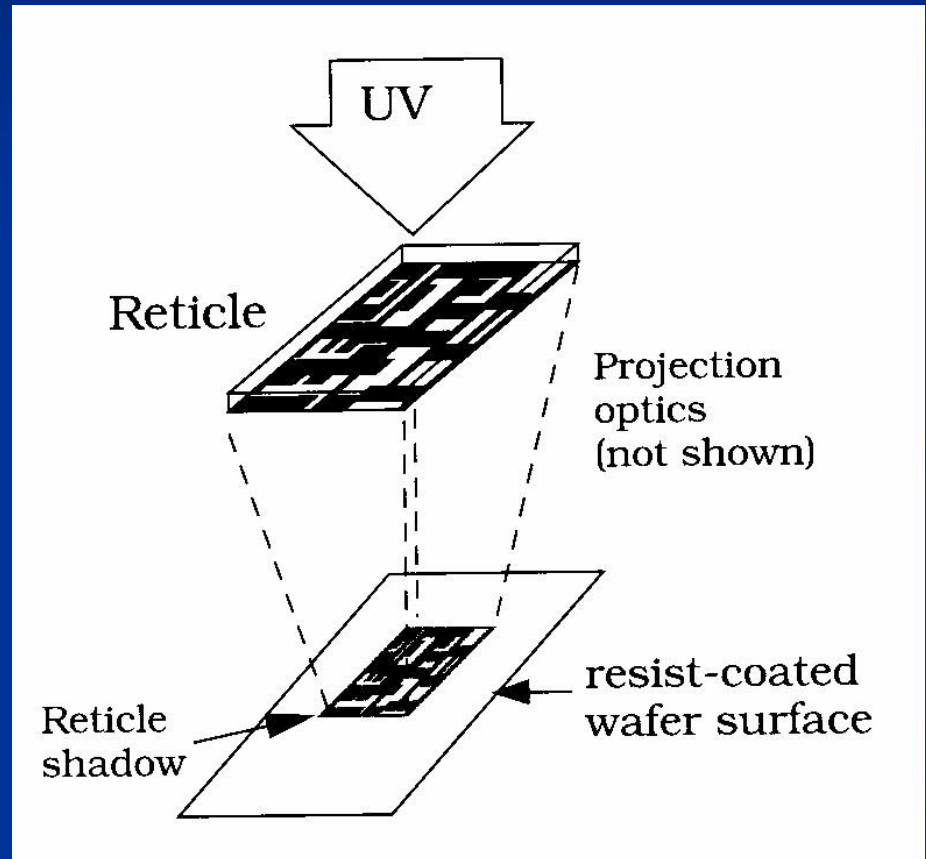
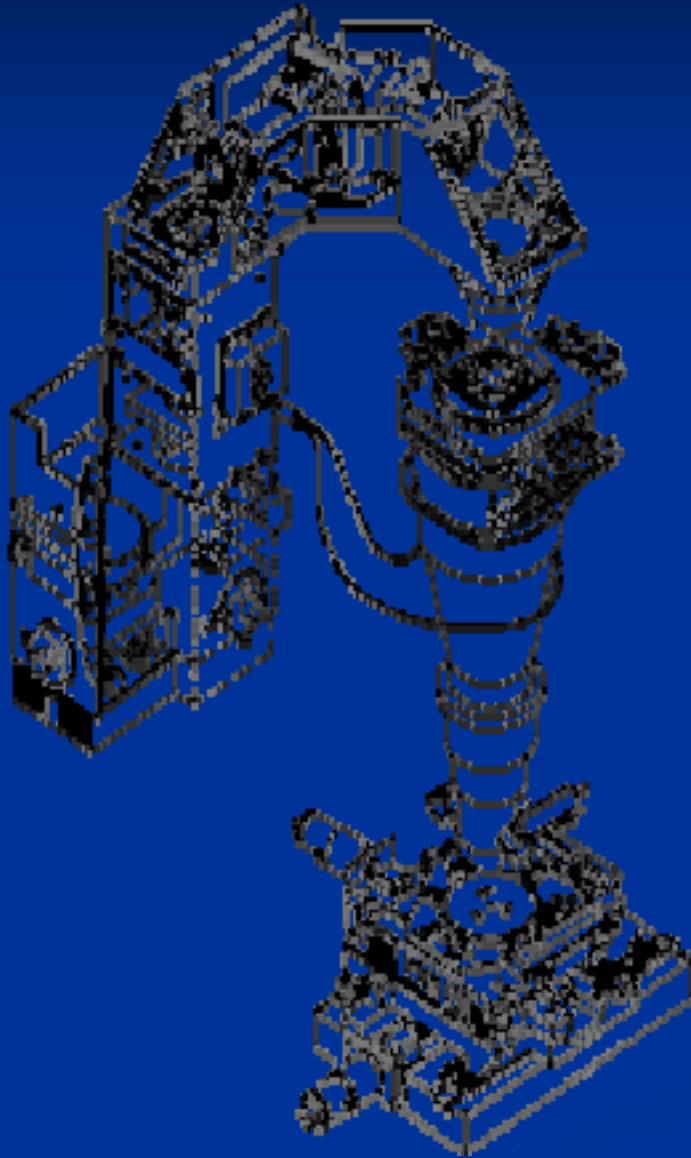


(c) Beading

# Patterning

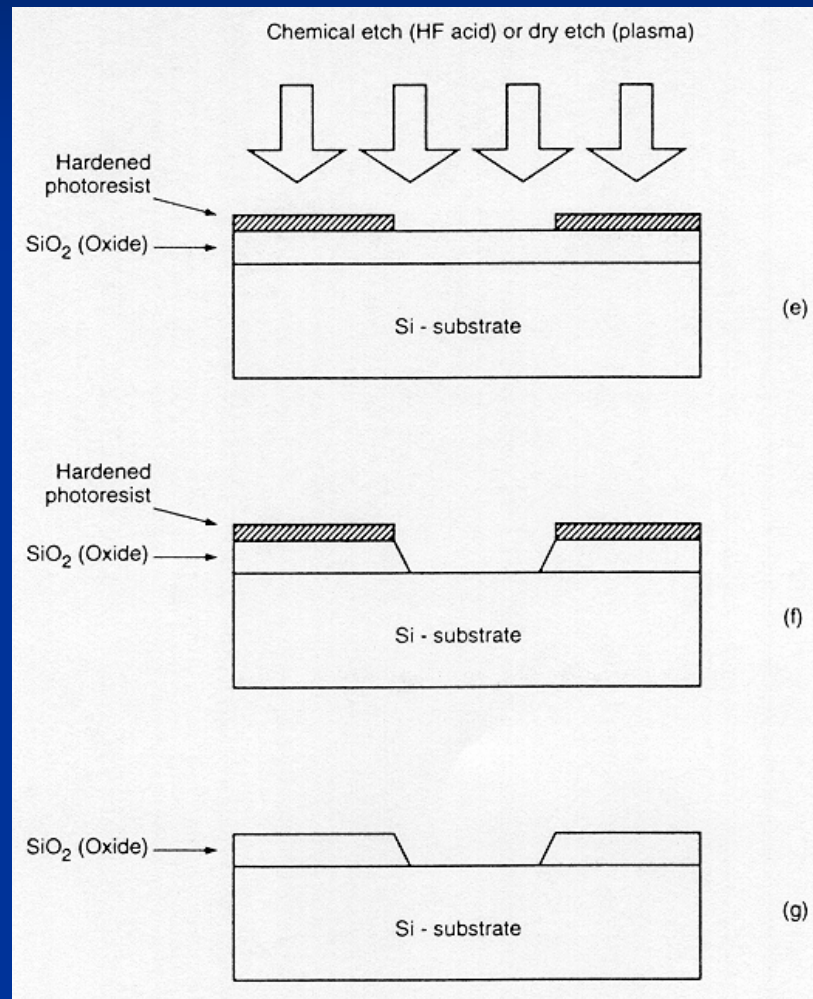


# Exposure



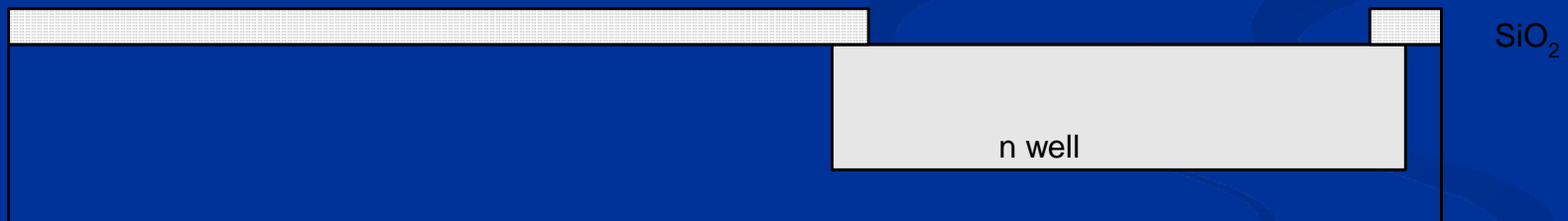


# Etching



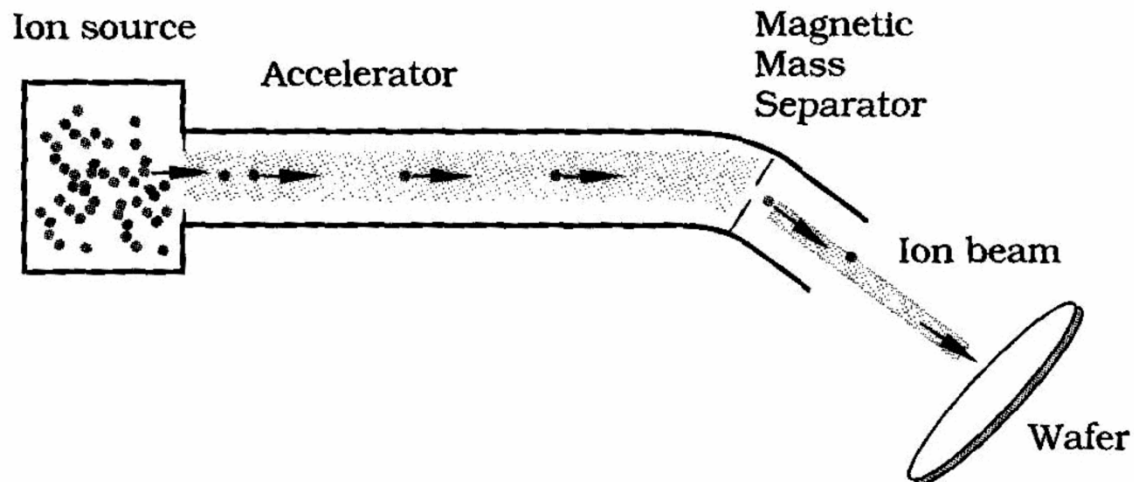
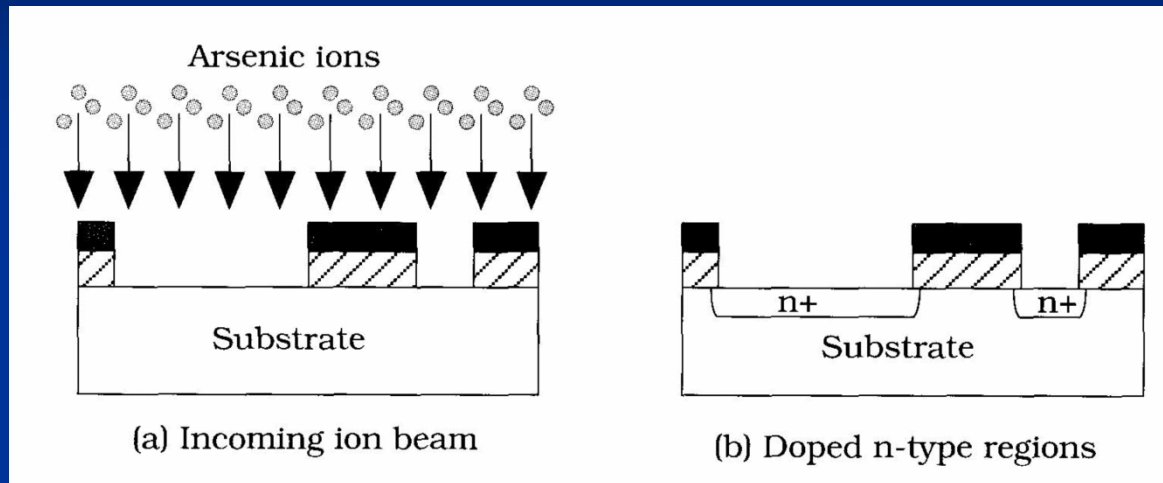
# Diffusion

- To create a n well:
  - Diffusion
    - Heat wafer in gas chamber until diffusion occurs.
  - Ion Implantation
    - Arsenic or phosphorous are implanted in window.

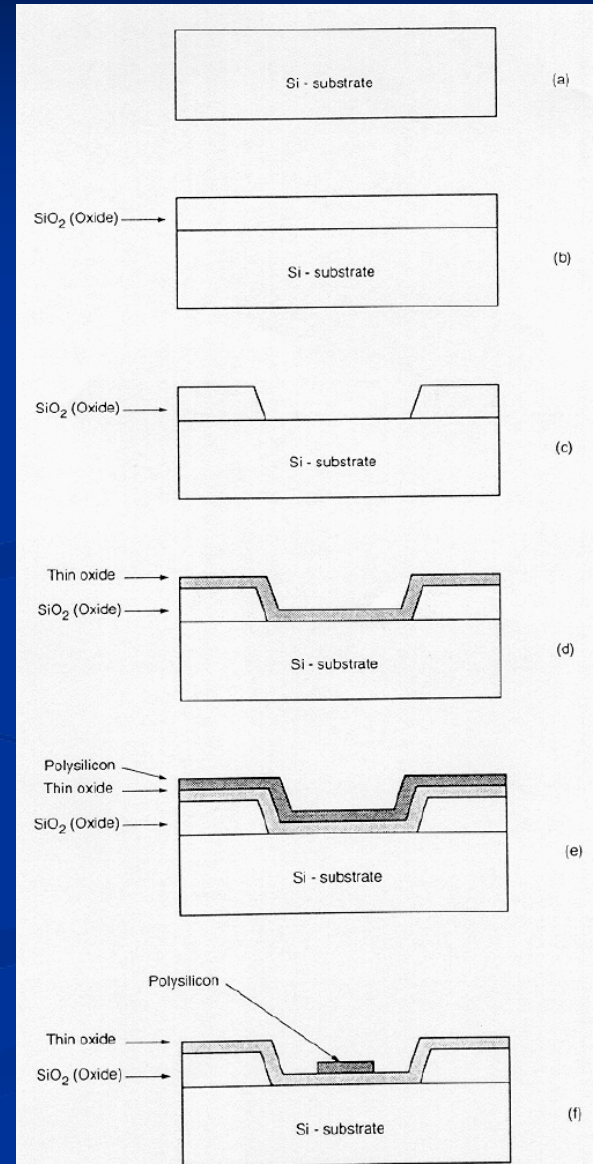
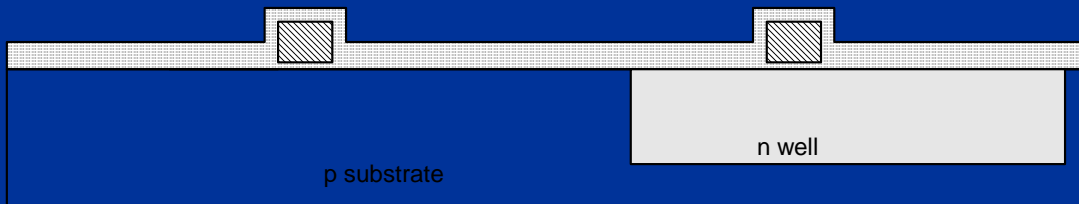




# Implantation

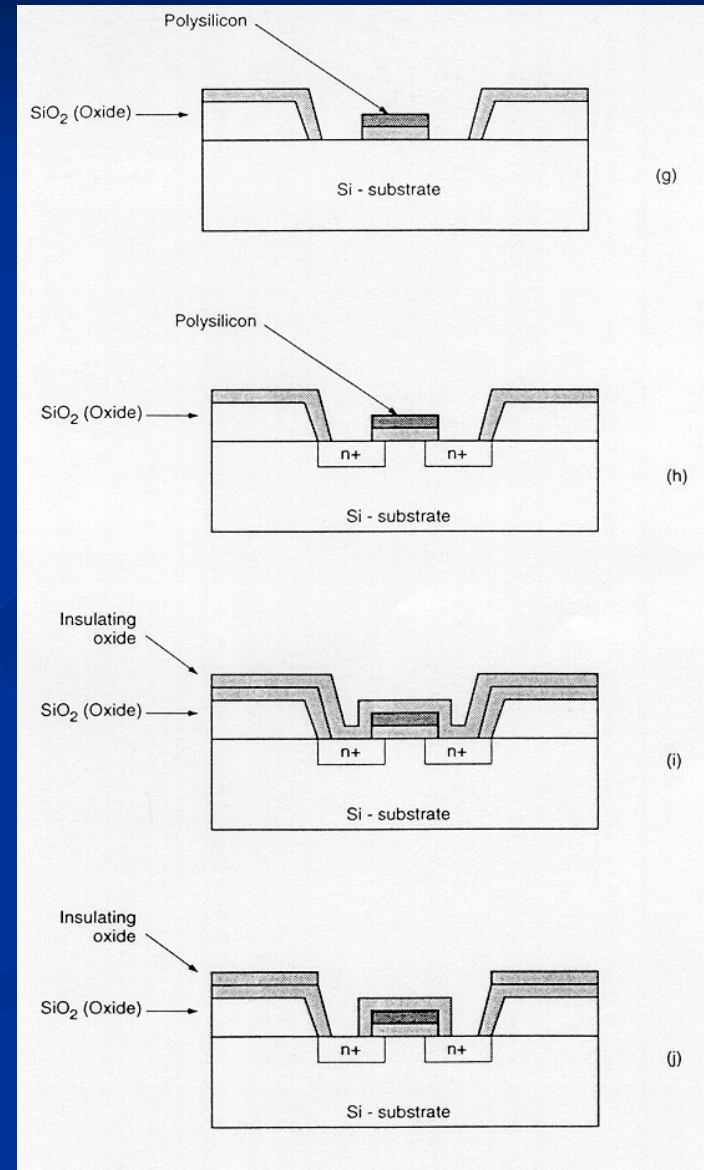


# Poly Deposition

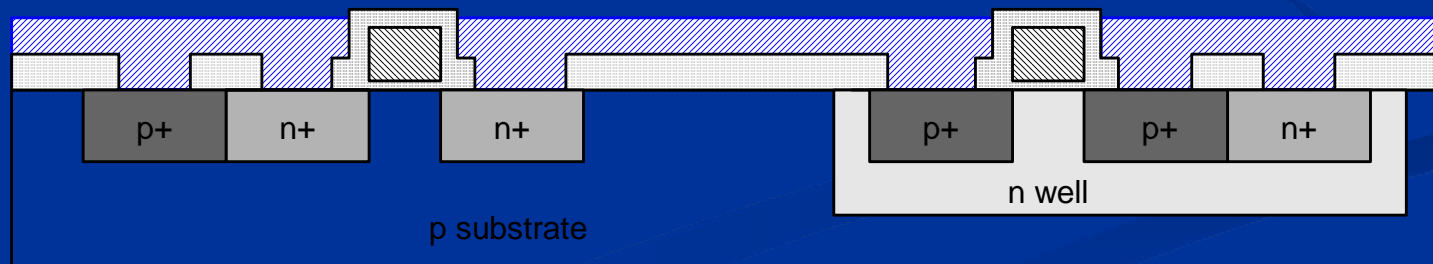
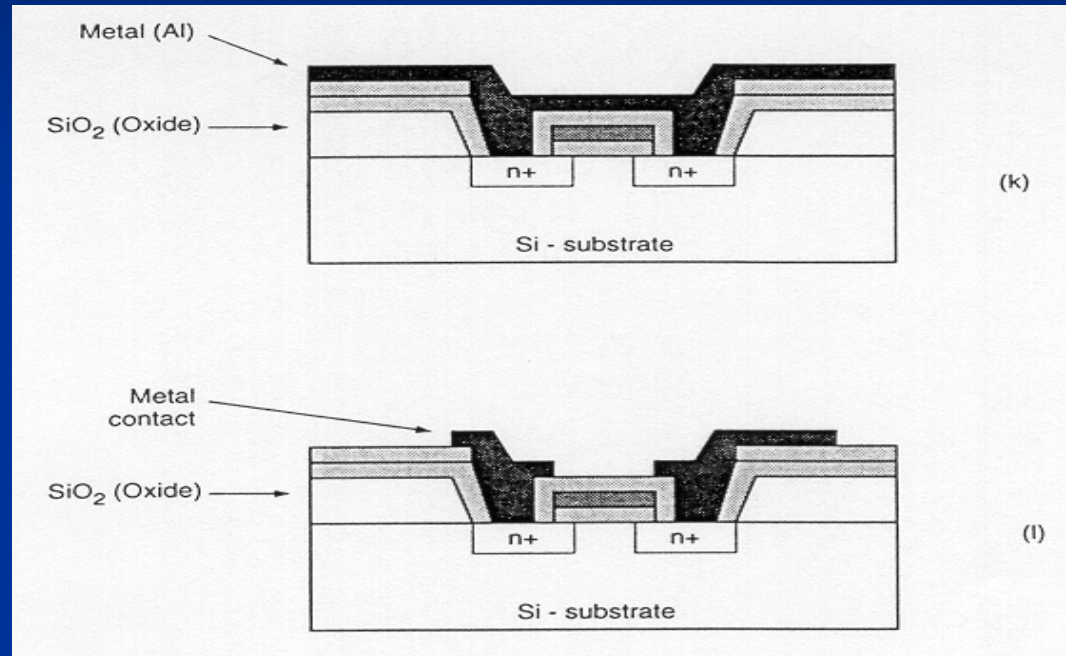


# Creating D and S

- Remove oxide layer using acid.
- Dope open area using Ion implantation or diffusion.



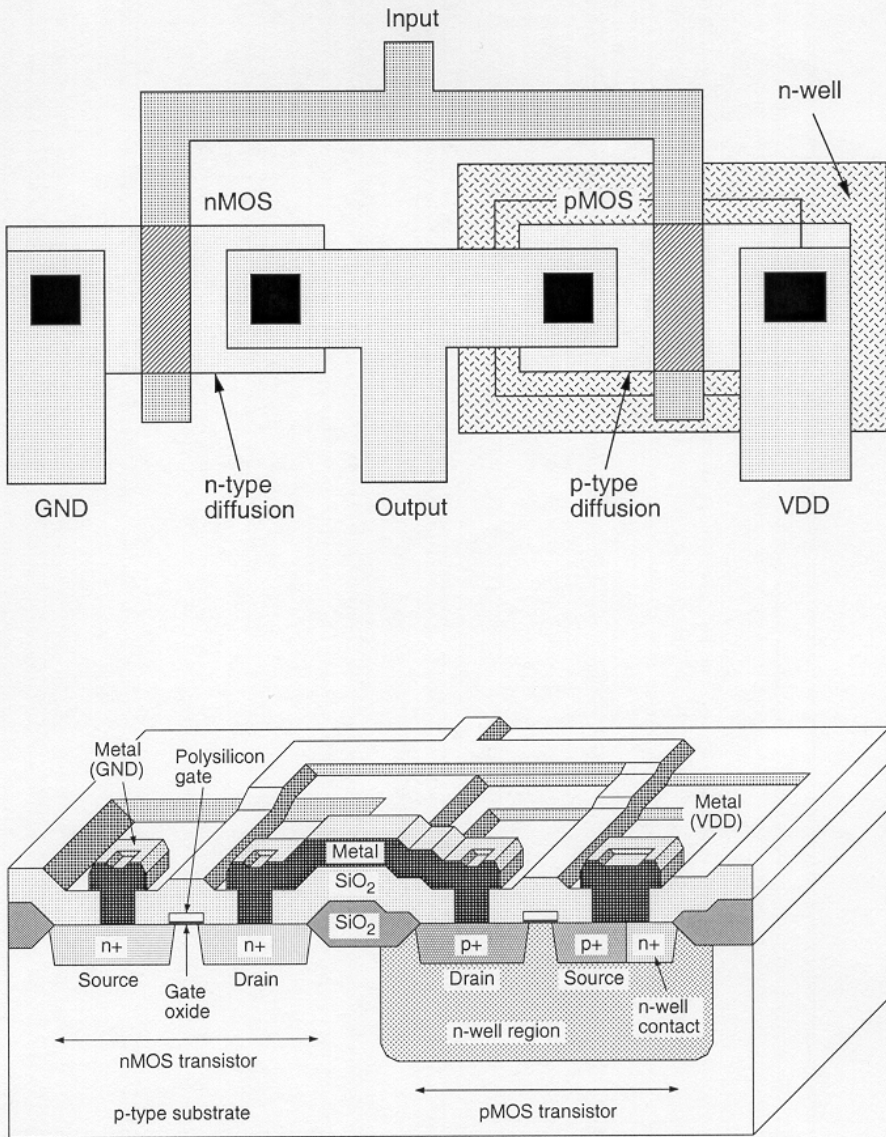
# Metal Deposition



Metal  
Thick field oxide



# Inverter



# Silicon on Insulator

